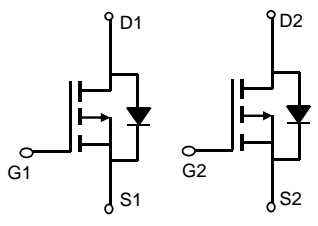
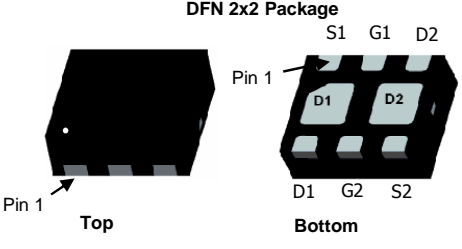


N-Channel Enhancement Mode Power MOSFET

<p>Description</p> <p>The HM2800D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a battery protection or in other switching application.</p> <p>General Features</p> <ul style="list-style-type: none"> ● $V_{DS} = 20V, I_D = 8.0A$ ● $R_{DS(ON)} < 40m\Omega @ V_{GS}=2.5V$ ● $R_{DS(ON)} < 33m\Omega @ V_{GS}=4.5V$ ● High power and current handling capability ● Lead free product is acquired ● Surface mount package <p>Application</p> <ul style="list-style-type: none"> ● Battery protection ● Load switch ● Power management 	 <p style="text-align: center;">Schematic diagram</p>  <p style="text-align: center;">DFN 2x2 Package</p>
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Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM2800D	HM2800D	DFN2X2-6L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current	$T_A = 25^\circ C$	I_D	8.0	A
	$T_A = 70^\circ C$		6.4	
Drain Current-Pulsed (Note 1)		I_{DM}	32	A
Maximum Power Dissipation		P_D	6.8	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	$^\circ C/W$
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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	22	-	V

Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.65	1.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=2.5V, I_D=4.0 A$	-	33	40	m Ω
		$V_{GS}=4.5V, I_D=4.5A$	-	22	33	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=4A$	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=8V, V_{GS}=0V,$ $F=1.0MHz$	-	500	-	PF
Output Capacitance	C_{oss}		-	300	-	PF
Reverse Transfer Capacitance	C_{rss}		-	140	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=1A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	20	40	nS
Turn-on Rise Time	t_r		-	18	40	nS
Turn-Off Delay Time	$t_{d(off)}$		-	60	108	nS
Turn-Off Fall Time	t_f		-	28	56	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=3A, V_{GS}=4.5V$	-	10	15	nC
Gate-Source Charge	Q_{gs}		-	2.3	-	nC
Gate-Drain Charge	Q_{gd}		-	2.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=1A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	1	A

Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature.
2. Surface mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

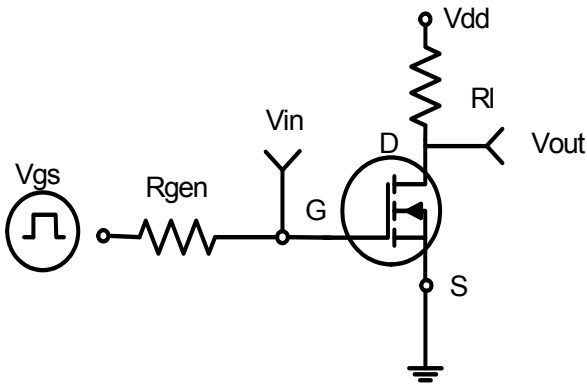


Figure 1: Switching Test Circuit

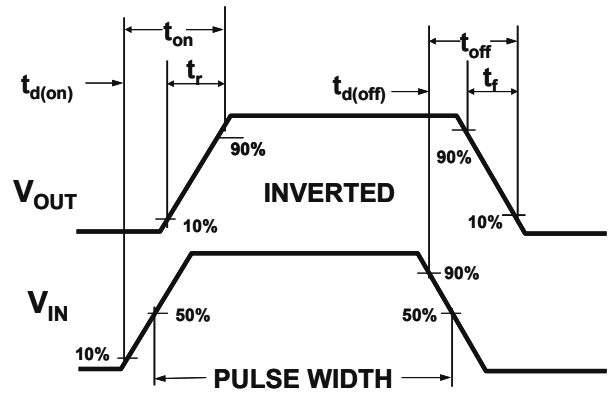
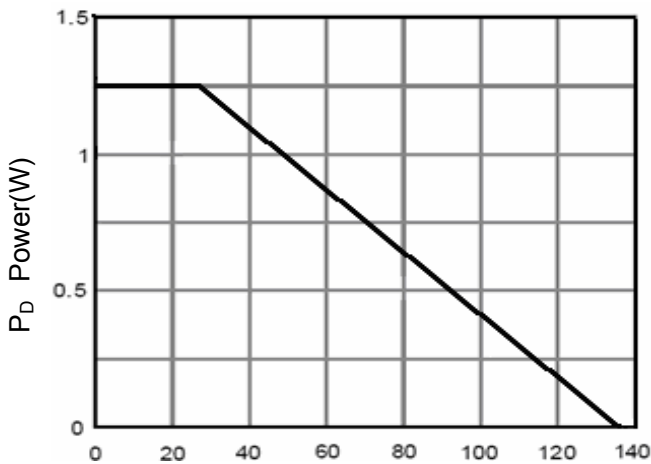
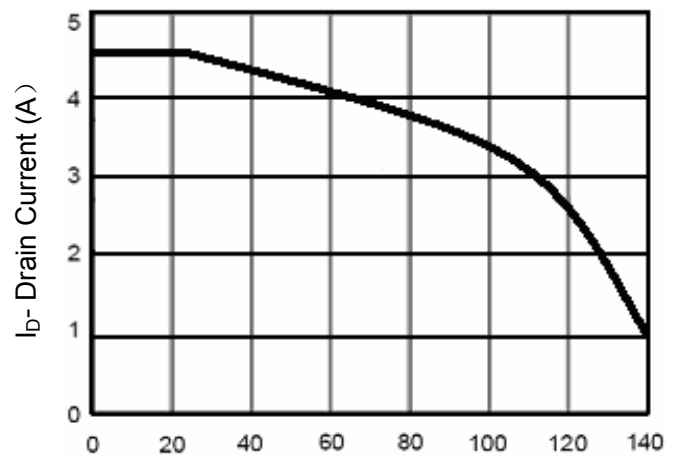


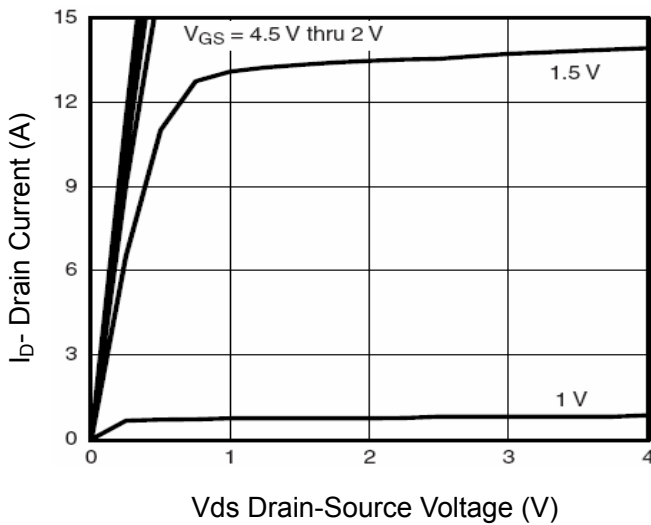
Figure 2: Switching Waveforms



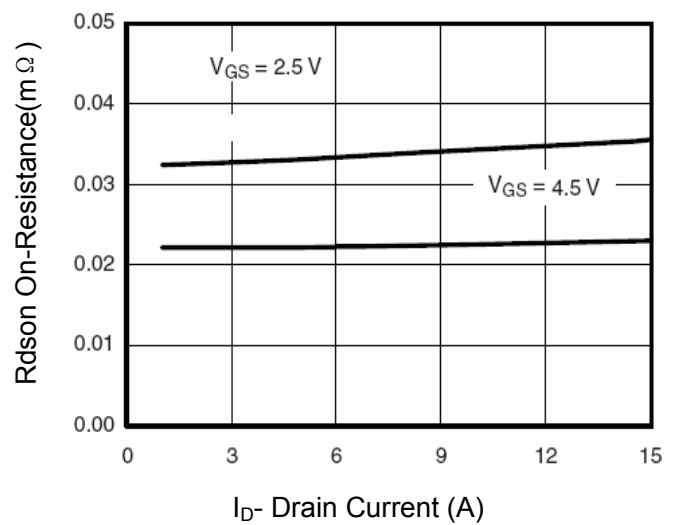
T_J-Junction Temperature(°C)
Figure 3 Power Dissipation



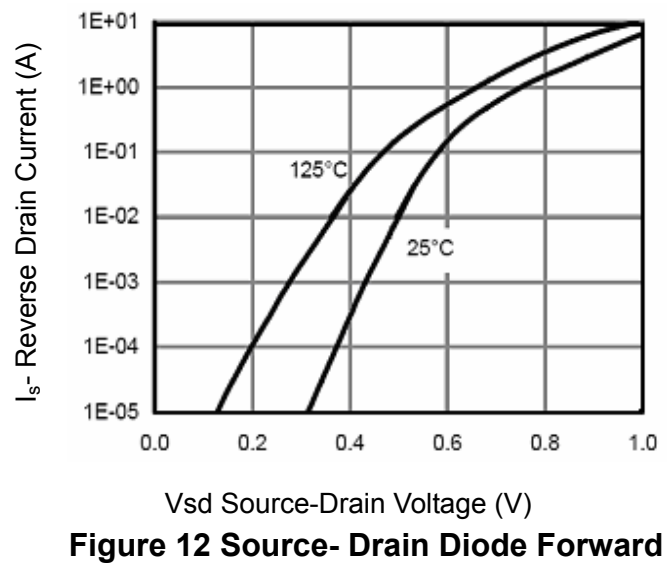
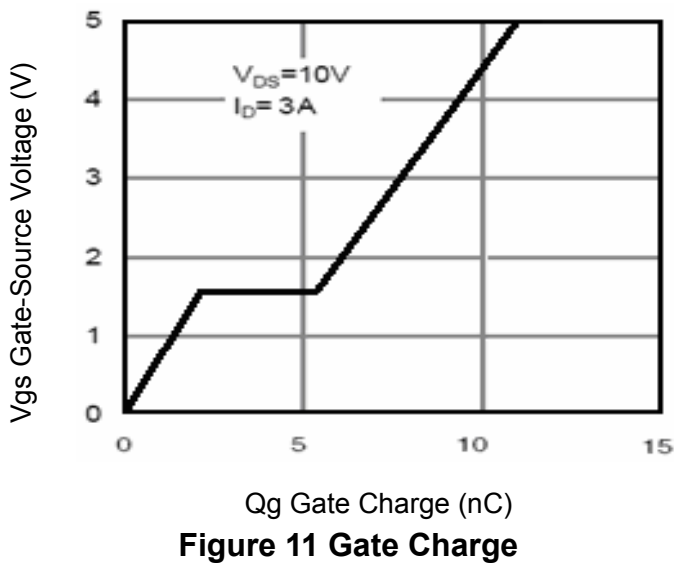
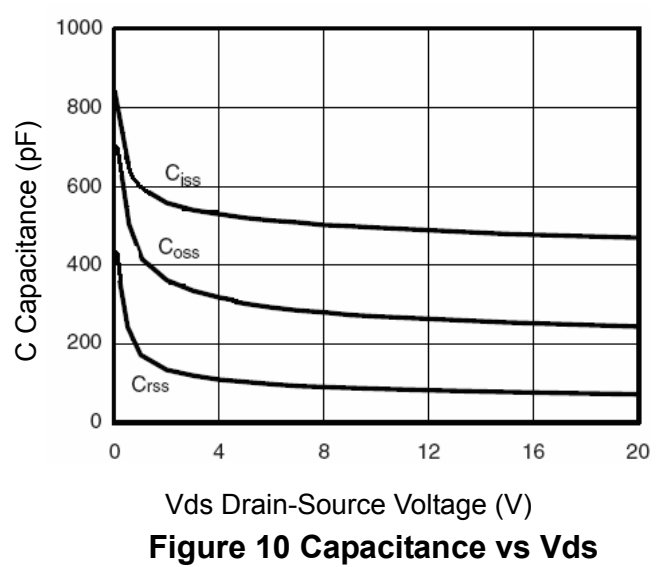
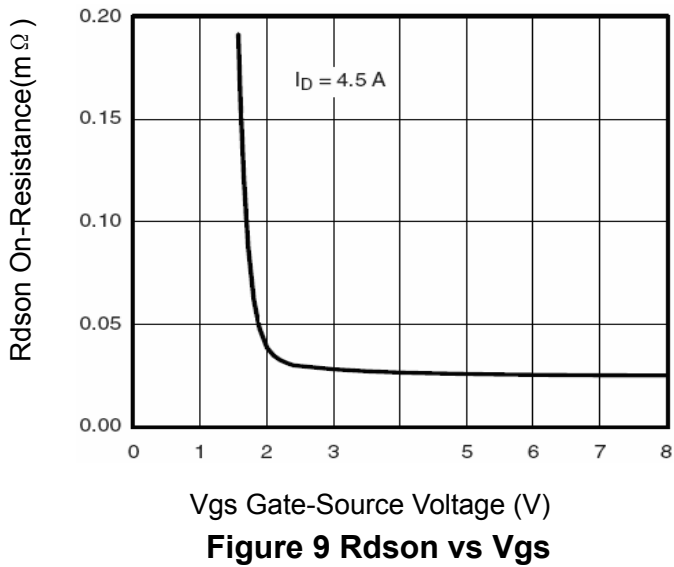
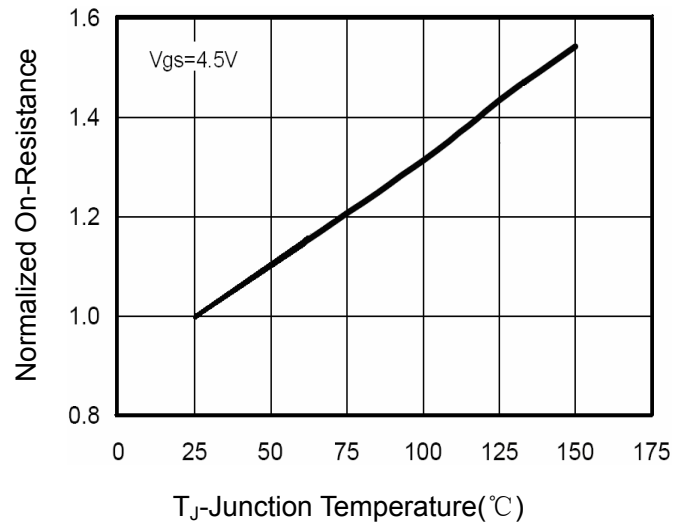
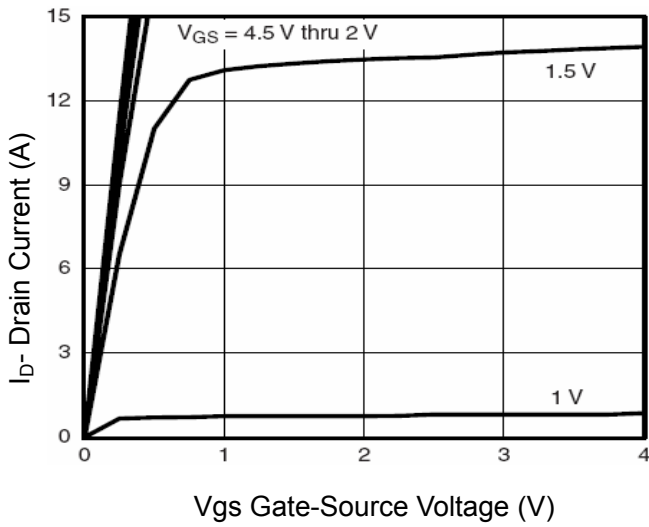
T_J-Junction Temperature(°C)
Figure 4 Drain Current



V_{DS} Drain-Source Voltage (V)
Figure 5 Output CHARACTERISTICS



I_D Drain Current (A)
Figure 6 Drain-Source On-Resistance



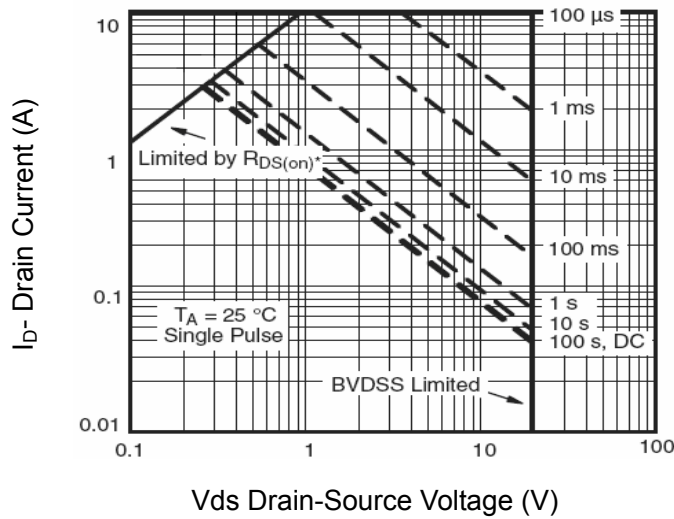


Figure 13 Safe Operation Area

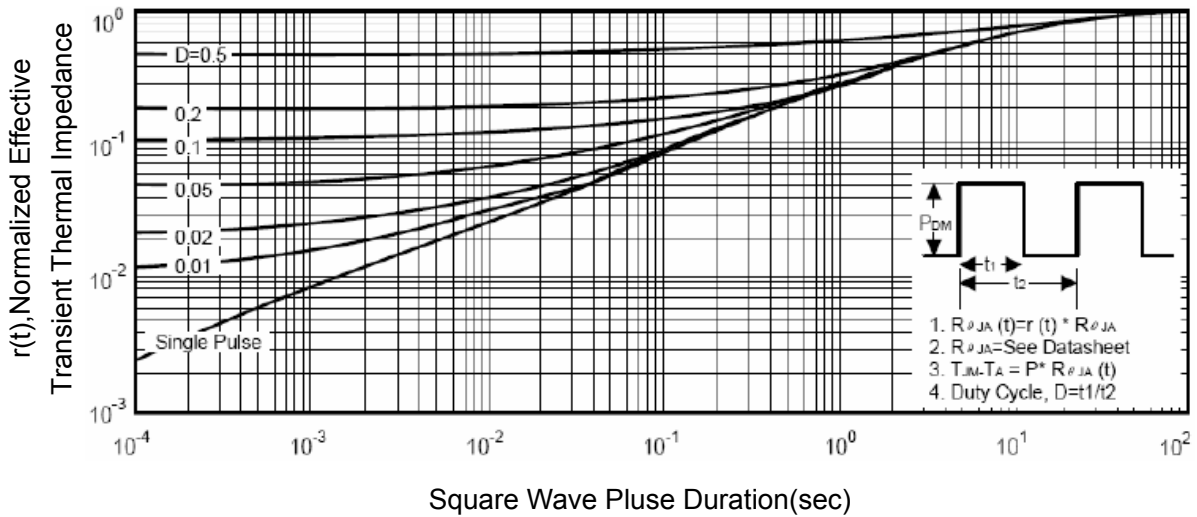
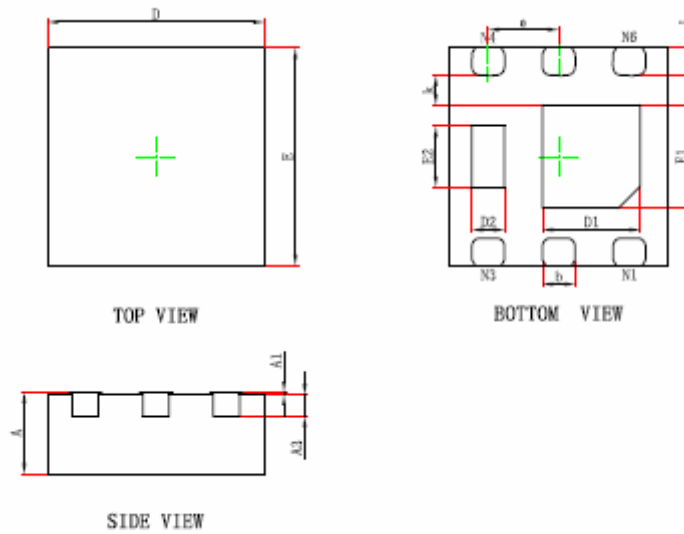


Figure 14 Normalized Maximum Transient Thermal Impedance

DFN2X2-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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